Erratum: Carrier-Controlled Ferromagnetism in SrTiO₃ [Phys. Rev. X **2**, 021014 (2012)]

Pouya Moetakef, James R. Williams, Daniel G. Ouellette, Adam P. Kajdos, David Goldhaber-Gordon,
S. James Allen, and Susanne Stemmer

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The inset in the original Fig. 2 shows the magnetization M as a function of magnetic field B at 2 K. The vertical axis in the original inset should have been labeled as showing the magnetization in units of μ_B per atom, not in units of μ_B/GdTiO_3 . In the corrected version of Fig. 2, shown here, the data is now plotted correctly in units of μ_B/GdTiO_3 . In the inset of the original Fig. 2, the linear contribution was subtracted to account for the substrate. For the inset in the corrected Fig. 2, the magnetization of the diamagnetic LSAT substrate and paramagnetic Ta backing layer was directly measured after removing the film by reactive ion etching. The magnetization as a function of magnetic field of the etched sample was subtracted from that of the sample with the GdTiO₃ thin film to obtain the inset in the corrected Fig. 2. The caption now contains additional information following the phrase “magnetic field at 2 K.” These corrections to the inset and caption for Fig. 2 do not affect any of the other results reported in the original paper, and all the conclusions in the paper remain unchanged.

FIG. 2. Magnetization as a function of temperature at 10 mT for a 4-nm GdTiO₃/1-nm SrTiO₃/4-nm GdTiO₃/LSAT heterostructure. The dotted line is a guide to the eye. The inset shows the magnetization M as a function of magnetic field at 2 K for the 8-nm GdTiO₃/1-nm SrTiO₃/LSAT heterostructure [same sample as shown in Fig. 1(b)].